

MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

SSM6K504NU

1. Applications

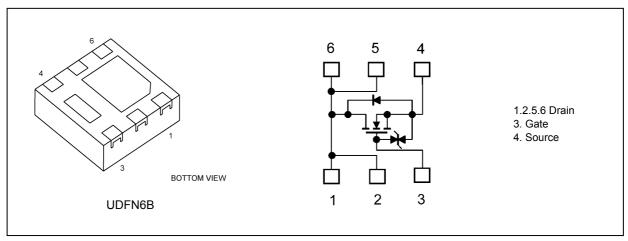
· High-Speed Switching

2. Features

- (1) 4.5 V gate drive voltage.
- (2) Low drain-source on-resistance
 - $R_{DS(ON)} = 26 \text{ m}\Omega \text{ (max) (@V_{GS} = 4.5 V)}$

 $R_{\rm DS(ON)}$ = 19.5 m Ω (max) (@V_{\rm GS} = 10 V)

3. Packaging and Pin Assignment



4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)		(Note 1)	I _D	9	Α
Drain current (pulsed)		(Note 1,2)	I _{DP}	18	
Power dissipation		(Note 3)	P _D	1.25	W
Power dissipation	$t \le 10 \text{ s}$	(Note 3)	P _D	2.5	W
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW) \leq 10 ms, duty \leq 1%
- Note 3: Device mounted on a FR4 board.

(25.4 mm \times 25.4 mm \times 1.6 mm, Cu Pad : 645 mm²)

Start of commercial production

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

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5. Electrical Characteristics

5.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_		±10	μА
Drain cut-off current		I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	
Drain-source breakdown voltage		V _{(BR)DSS}	I_D = 10 mA, V_{GS} = 0 V	30			V
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I_D = 10 mA, V_{GS} = -20 V	15			
Gate threshold voltage	(Note 2)	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 0.1 \text{ mA}$	1.3		2.5	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	$I_D = 4.0 \text{ A}, V_{GS} = 4.5 \text{ V}$		19	26	mΩ
			$I_D = 4.0 \text{ A}, V_{GS} = 10 \text{ V}$	_	14	19.5	
Forward transfer admittance	(Note 3)	Y _{fs}	V _{DS} = 10 V, I _D = 2.0 A	_	20	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (0.1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

Take this into consideration when using the device.

Note 3: Pulse measurement.

5.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V,	_	620	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	42	_	
Output capacitance	Coss		_	110	_	
Gate resistance	r _g		_	8	_	Ω
Switching time (turn-on time)	t _{on}	V_{DD} = 15 V, I_{D} = 1.0 A V_{GS} = 0 to 4.5 V, R_{G} = 10 Ω ,	_	26.0	_	ns
Switching time (turn-off time)	t _{off}	Duty ≤ 1%, Input: t _r , t _f < 5 ns Ground source, See Chapter 5.3	_	16.4	_	

5.3. Switching Time Test Circuit

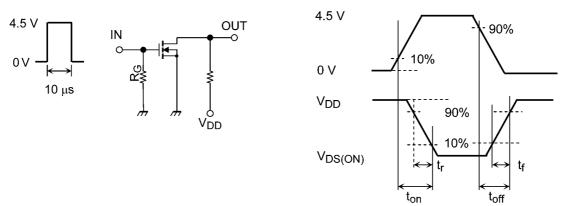


Fig. 5.3.1 Test Circuit of Switching Time

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V _{DD} = 15 V, V _{GS} = 4.5 V,	_	4.8	_	nC
Gate-source charge 1	Q _{gs1}	I _D = 9.0 A	_	2.7		
Gate-drain charge	Q_{gd}		_	1.6		



5.5. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	I _D = -4.0 A, V _{GS} = 0 V		-0.85	-1.2	V

Note 1: Pulse measurement.

6. Marking

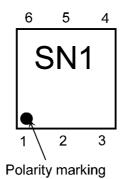
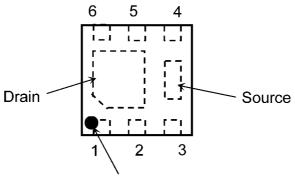


Fig. 6.1 Marking



Polarity marking (on the top)

*Electrodes : on the bottom

Fig. 6.2 Pin Condition(Top View)

7. Characteristics Curves (Note)

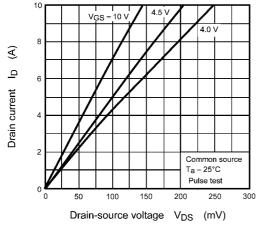


Fig. 7.1 I_D - V_{DS}

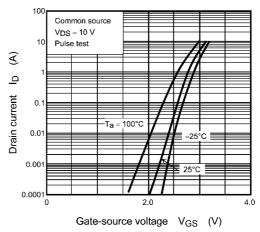


Fig. 7.2 I_D - V_{GS}

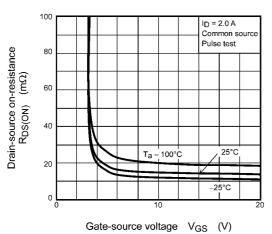


Fig. 7.3 R_{DS(ON)} - V_{GS}

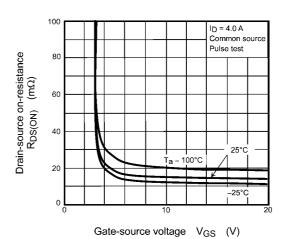


Fig. 7.4 R_{DS(ON)} - V_{GS}

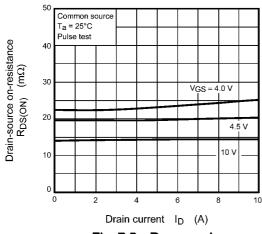


Fig. 7.5 R_{DS(ON)} - I_D

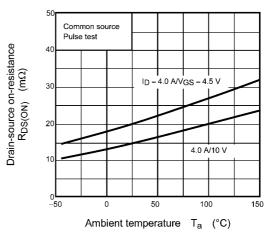


Fig. 7.6 R_{DS(ON)} - T_a

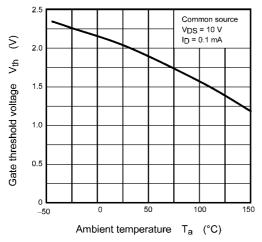
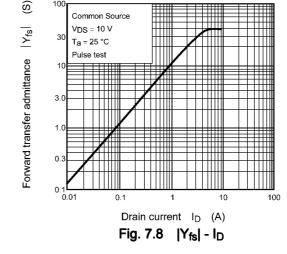


Fig. 7.7 V_{th} - T_a



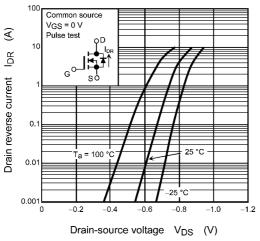


Fig. 7.9 IDR - VDS

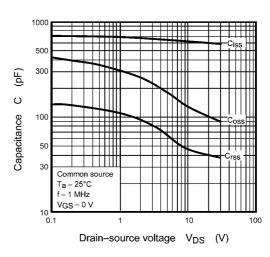


Fig. 7.10 C - V_{DS}

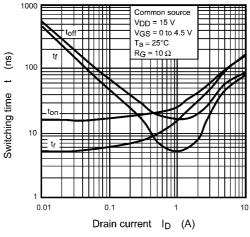


Fig. 7.11 t-I_D

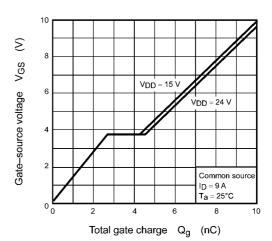


Fig. 7.12 Dynamic Input Characteristics

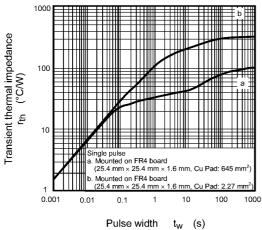


Fig. 7.13 $r_{th} - t_w$

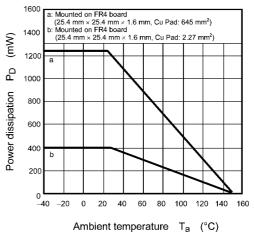


Fig. 7.14 PD - Ta

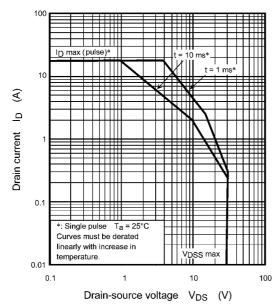


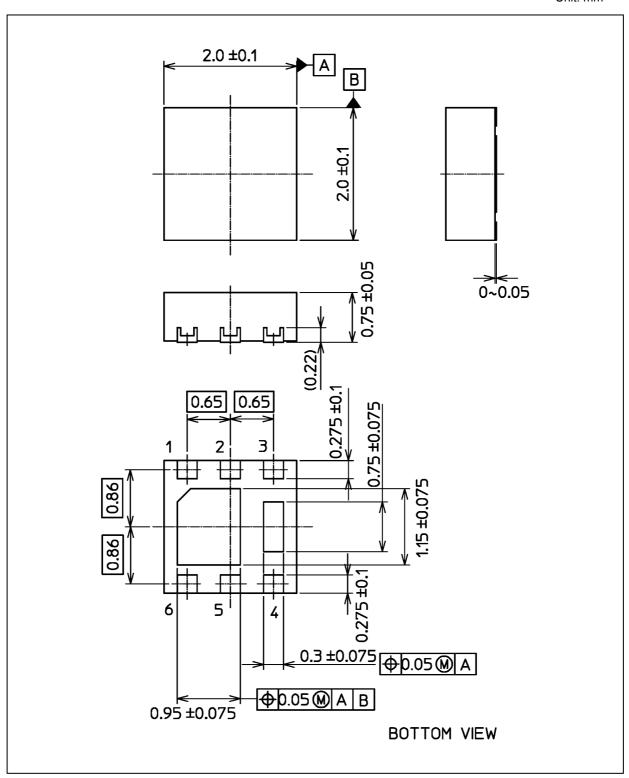
Fig. 7.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
TOSHIBA: 2-2AA1A	
Nickname: UDFN6B	



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